

Please amend the specification as follows:

In the Claims:

Please ~~cancel~~ nonelected Claims 7 and 8 without prejudice.

Please amend the Claims as follows:

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- a1
1. (amended) A semiconductor device, comprising:  
a contact pad on a semiconductor substrate;  
a conductive bump on said contact pad, said bump comprising a coaxially-aligned stack of bodies having different cross-sectional dimensions, said bodies at the top of said stack having smaller cross-sectional dimensions.
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Please add the following new claims:

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9. (new) The semiconductor device of Claim 1, wherein said bodies at the top of said stack have a smaller height dimension than lower bodies in said stack.

a2

10. (new) The semiconductor device of Claim 1, further comprising a barrier layer between said conductive bump and said contact pad.

11. (new) The semiconductor device of Claim 1, further comprising a passivating film around said contact pad.

12. (new) The semiconductor device of Claim 1, wherein said contact pad is on an insulating film on said semiconductor substrate.

13. (new) A semiconductor device, comprising:  
a contact pad on an insulating film on a semiconductor substrate;

a barrier layer on said contact pad;  
a first bump on said barrier layer having a first cross-sectional dimension;  
a second bump on and coaxially aligned with said first bump, said second bump having a cross-sectional dimension smaller than said first cross-sectional dimension.

14. (new) The semiconductor device of Claim 13, further comprising a passivating film around said contact pad.

A2  
15. (new) The semiconductor device of Claim 13, wherein said first bump has a first height dimension and said second bump has a second height dimension, wherein said first height dimension is greater than said second height dimension.

16. (new) The semiconductor device of Claim 13, wherein said first and second bumps are circular.

17. (new) The semiconductor device of Claim 13, wherein said bumps are made of gold.

18. (new) A semiconductor device, comprising:

a semiconductor substrate, said substrate including:  
a contact pad on said semiconductor substrate;  
a first bump on said contact pad;  
a smaller second bump on said first bump, said second bump coaxially aligned with said first bump and having a substantially flat peak plane;  
a printed circuit board, wherein said semiconductor substrate is mounted over said printed circuit board such that said contact pad and said first and second bumps are aligned with a conductive film on said printed circuit board.

19. (new) The semiconductor device of Claim 18, further comprising a passivating film around said contact pad.

20. (new) The semiconductor device of Claim 18, wherein said first bump has a first height dimension and said second bump has a second height dimension, wherein said first height dimension is greater than said second height dimension.

21. (new) The semiconductor device of Claim 18, wherein said first and second bumps are circular.

22. (new) The semiconductor device of Claim 18, wherein said bumps are made of gold.

#### REMARKS

Reconsideration of the above-referenced application in view of the amendments and the following remarks is respectfully requested.

Claims 1-8 were pending in this case. The election by Applicant to prosecute Claims 1-6 is hereby affirmed. Nonelected Claims 7 and 8 are hereby cancelled without prejudice. New Claims 9-22 have been added. Claim 1 has been amended to more clearly define the scope of the claimed invention.

Claims 1-3 stand rejected under 35 U.S.C. 102(b) as being anticipated by Yamada, et al. (U.S. Patent No. 5,864,174). Claim 1, as amended, includes the feature of "a contact pad on a semiconductor substrate" as well as "a conductive bump on said contact pad, said bump comprising a coaxially-aligned stack of bodies having different cross-sectional dimensions, said bodies at the top of said stack having smaller cross-sectional dimensions." In contrast, in Yamada's Figure 21c, the smallest ball 33a in the stack of the three balls 33a, 33b, and 33c is on electrode 32 on semiconductor element 31. Indeed, Yamada says at column 11, lines 61-64, that the one ball of the stack that is joined to electrode